

Novel Refractory Semiconductors: Symposium, April 21–23, 1987, Anaheim, California, U.S.A.

1. Icosahedral Boron-Rich Solids as Refractory Semiconductors — David Emin.
2. Electron Transport in Boron-Rich Borides — O. A. Golikova.
3. Anomalous Seebeck Coefficient in Boron Carbides — T. L. Aselage, D. Emin, C. Wood, I. Mackinnon, I. Howard.
4. Electronic Transport Properties of Hot-Pressed B₆Si — C. Wood, D. Emin, R. S. Feigelson, I. D. R. Mackinnon.
5. Origin of Paramagnetic Defect in Single Crystal and Ceramic B₄C — E. L. Venturini, D. Emin, T. L. Aselage.
6. Nature of Paramagnetic Centers in Amorphous Boron — G. P. Tsiskarishvili et al.
7. Thermal Properties of Boron-Rich Borides — H. E. Fischer, E. T. Swartz, P. R. H. Türkes, R. O. Pohl.
8. Thermal Conductivity of Boron Carbides — Marvin Moss.
9. Microscopic Origin of the Composition-Dependent Change of the Thermal Conductivity in Boron Carbides — David Emin, I. A. Howard, T. A. Green, C. L. Beckel.
10. A Theoretical Approach to the Thermal Conductivity of Boron Carbides — V. M. Kenkre, X. Fan.
11. Atomic Interactions in a Boron-Rich Carbon-Containing Icosahedron: Para-Carborane — C. L. Beckel, G. E. Obarski, M. Z. Fuka, J. D. Fritts.
12. Preparation of Boron-Rich Refractory Semiconductors — T. L. Aselage.
13. Low-Carbon Boron Carbides Produced by CVD — A. N. Campbell, A. W. Mullendore, D. R. Tallant, C. Wood.
14. Crystal Structure Refinements of Rhombohedral Symmetry Materials Containing Boron-Rich Icosahedra — B. Morosin, T. L. Aselage, R. S. Feigelson.